TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (DTMOS II)

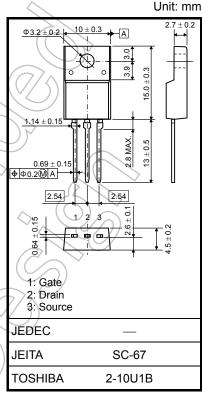
# **TK13A65U**

### Switching Regulator Applications

- Low drain-source ON resistance: RDS (ON) =  $0.32 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 8.0 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 100 \,\mu\text{A} \,(\text{max}) \,(V_{DS} = 650 \,\text{V})$
- Enhancement-mode:  $V_{th} = 3.0 \text{ to } 5.0 \text{ V (VDS} = 10 \text{ V, ID} = 1 \text{ mA)}$

### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                        |       | Symbol    | Rating           | Unit       |                   |
|--|-------|-----------|------------------|------------|-------------------|
| Drain-source voltage                   |       | $V_{DSS}$ | 650              | (X)        |                   |
| Gate-source voltage                    |       |           | V <sub>GSS</sub> | ±30        | $\langle \rangle$ |
| Drain current                          | DC    | (Note 1)  | ΙD               | 13         | A                 |
|  | Pulse | (Note 1)  | $I_{DP}$         | 26         | ~                 |
| Drain power dissipation (Tc = 25°C)    |       |           | $P_{D}$          | 40         | W                 |
| Single pulse avalanche energy (Note 2) |       |           | E <sub>AS</sub>  | 86         | mJ                |
| Avalanche current                      |       |           | I <sub>AR</sub>  | 13         | A                 |
| Repetitive avalanche energy (Note 3)   |       |           | EAR              | 4.0        | E)                |
| Channel temperature                    |       |           | T <sub>ch</sub>  | )) 150     | °C                |
| Storage temperature range              |       |           | T <sub>stg</sub> | -55 to 150 | O°C               |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Thermal Characteristics

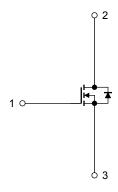
| Characteristics                        | Symbol     | Max   | Unit |
|--|------------|-------|------|
| Thermal resistance, channel to case    | Rth (ch-c) | 3.125 | °C/W |
| Thermal resistance, channel to ambient | Rth (ch-a) | 62.5  | °C/W |

Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 0.9 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 13 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



Internal Connection

Start of commercial production 2009-03

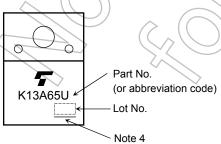
## **Electrical Characteristics (Ta = 25°C)**

| Chara                             | acteristics            | Symbol               | Test Condition  | Min        | Тур. | Max      | Unit |
|-----------------------------------|------------------------|----------------------|---|------------|------|----------|------|
| Gate leakage current              |                        | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$                         | _          | _    | ±1       | μА   |
| Drain cut-off curre               | ent                    | I <sub>DSS</sub>     | V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V                            | _          | _    | 100      | μА   |
| Drain-source brea                 | akdown voltage         | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                             | 650        | _    | _        | V    |
| Gate threshold vo                 | Gate threshold voltage |                      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                             | 3.0        | _    | 5.0      | ٧    |
| Drain-source ON resistance        |                        | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.5 A                            | (F         | 0.32 | 0.38     | Ω    |
| Forward transfer admittance       |                        | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.5 A                            | 2.0        | 8.0  | _        | S    |
| Input capacitance                 |                        | C <sub>iss</sub>     |   | ()         | 950  | _        |      |
| Reverse transfer capacitance      |                        | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                  | _          | 47   | _        | pF   |
| Output capacitance                |                        | C <sub>oss</sub>     |   | 7 —        | 2300 | _        |      |
| Switching time                    | Rise time              | t <sub>r</sub>       | 10 V ID = 6.5 A VOUT  | _          | 30   | <i> </i> |      |
|                                   | Turn-ON time           | t <sub>on</sub>      | 0 V   |            | 65   | > _      | ns   |
|                                   | Fall time              | t <sub>f</sub>       | ///<br>V <sub>DD</sub> ≈ 200 V  |            | 8    | ) —      | 113  |
|                                   | Turn-OFF time          | t <sub>off</sub>     | Duty $\leq 1\%$ , $t_W = 10 \mu s$  | (2)        | 80   | _        |      |
| Total gate charge Qg              |                        | Qg                   |   |            | 17   | _        |      |
| Gate-source charge                |                        | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$ | <i>)</i> – | 10   | _        | nC   |
| Gate-drain charge Q <sub>gd</sub> |                        | Q <sub>gd</sub>      |   | _          | 7    | _        |      |

# Source-Drain Ratings and Characteristics (Ta = 25°C)

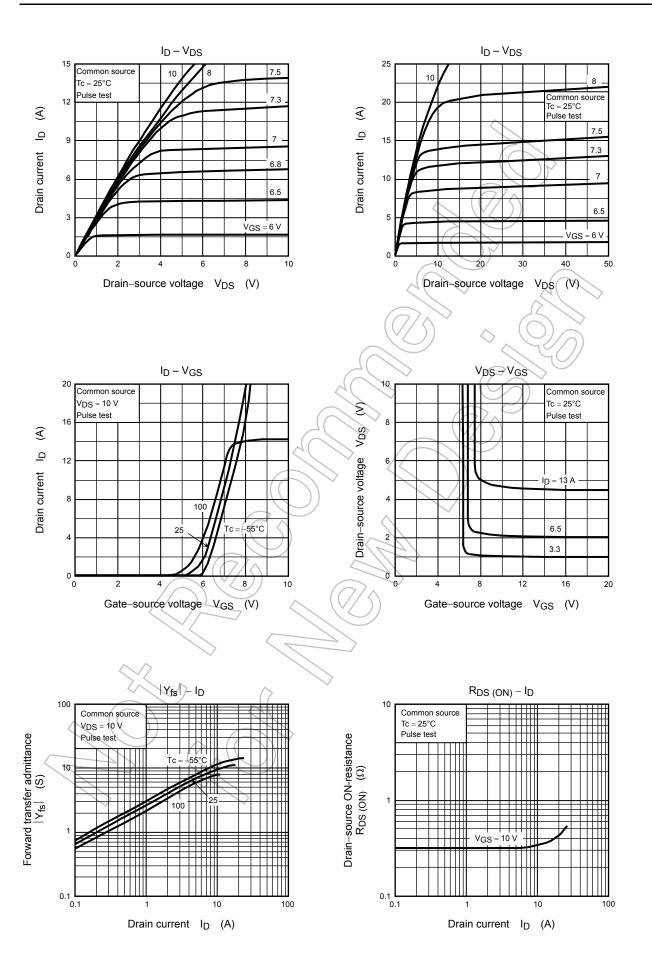
| Characteristics                           | Symbol             | Test Condition                                 | Min | Тур. | Max  | Unit |
|---|--------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | )) I <sub>DR</sub> |  | _   | _    | 13   | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub>   | ((// 5) -                                      | _   | _    | 26   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub>   | I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | trr                | I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V, | _   | 430  | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>    | dl <sub>DR</sub> /dt = 100 A/μs                | _   | 7.0  | _    | μС   |

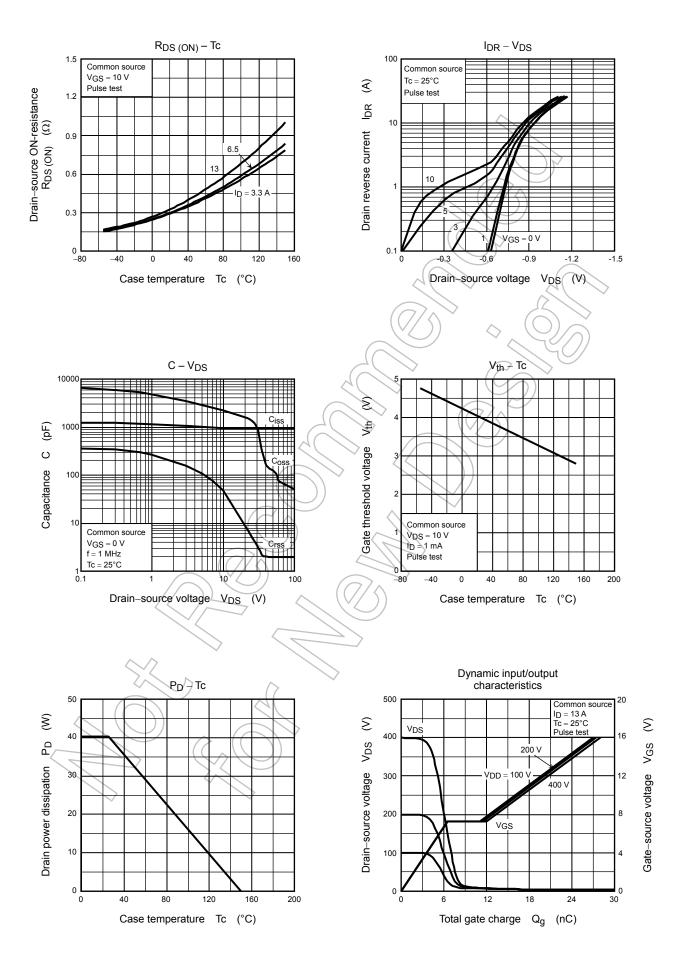
#### **Marking**

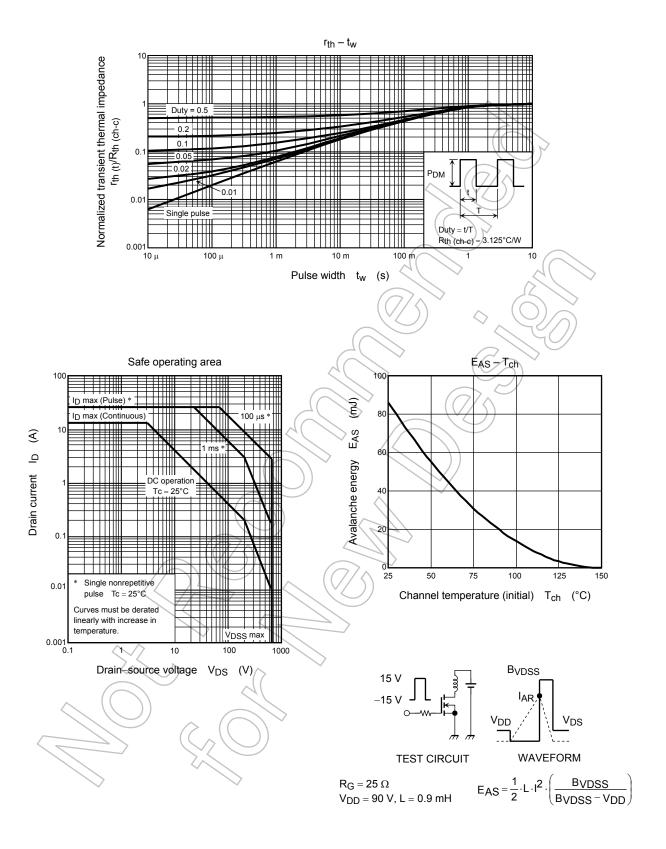


Note 4 : A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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